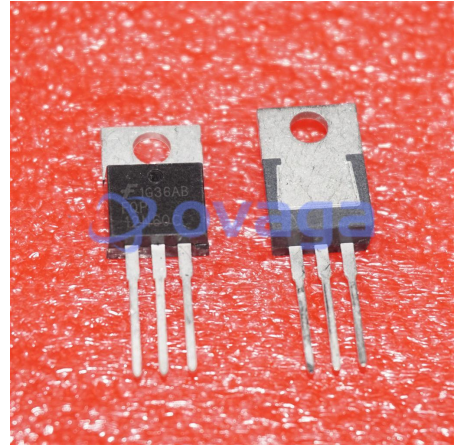


MOSFET, N, Transistor Polarity:N Channel, Continuous Drain Current Id:12A, Drain Source Voltage Vds:600V, On Resistance Rds(on):530mohm, Rds(on) Test Voltage Vgs:10V, Threshold Voltage Vgs:4V, Power Dissipation Pd:225W, MSL:-



Images are for reference only

Manufacturers	<u>NXP Semiconductor</u>
Package/Case	TO-220
Product Type	Transistors
RoHS	Green
Lifecycle	

Please submit RFQ for FQP12N60C or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

FQP12N60C is a MOSFET transistor, specifically an N-channel power MOSFET, produced by Fairchild Semiconductor.

Features

Drain-Source Voltage: 600V

Continuous Drain Current: 12A

Power Dissipation: 90W

Gate-Source Voltage (max): ±30V

Low on-resistance

Fast switching speed

High input impedance

Application

Switching power supplies

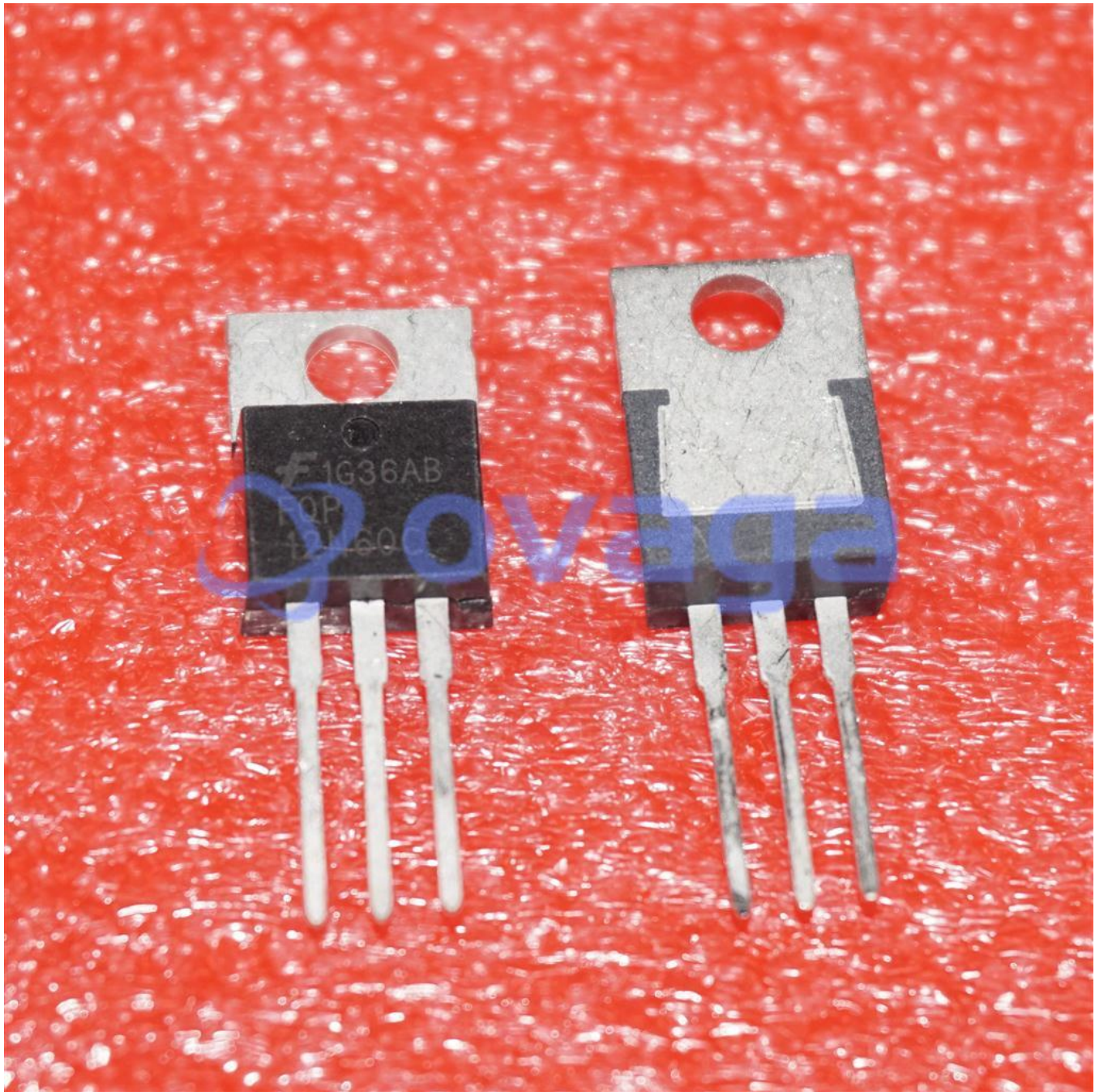
Motor control circuits

Lighting ballasts

Audio amplifiers

DC-DC converters

Solar inverters



Related Products



[FQA28N50F](#)

NXP Semiconductor
TO-3PN



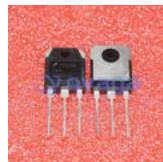
[FQP9N50C](#)

NXP Semiconductor
TO-220-3



[FQP18N50V2](#)

NXP Semiconductor
TO-220



[FQA24N50F](#)

NXP Semiconductor
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